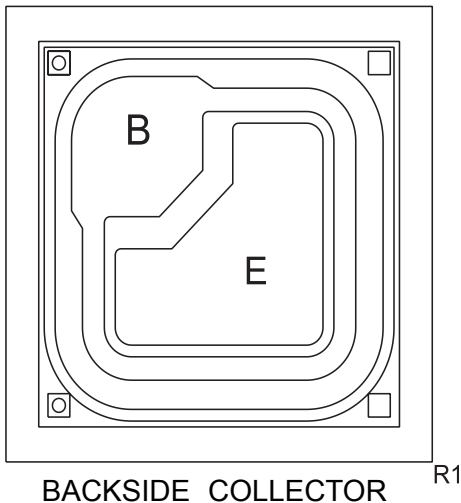


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	15 x 15 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	4.0 x 4.0 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

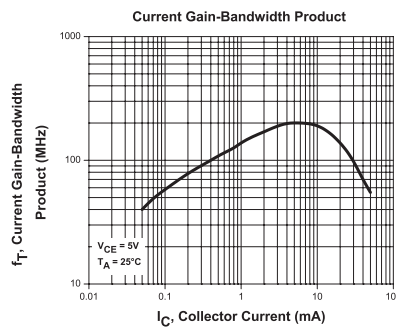
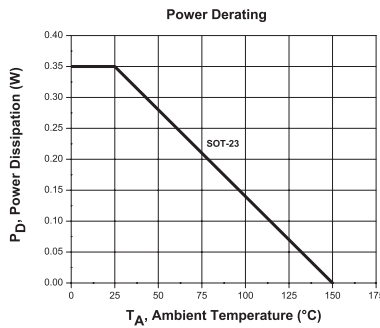
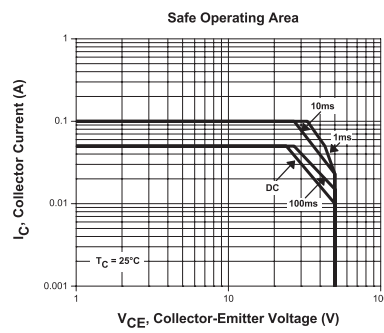
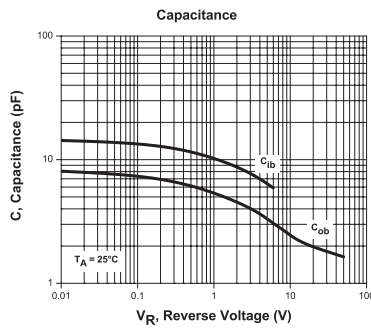
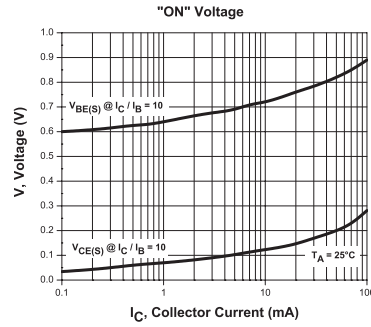
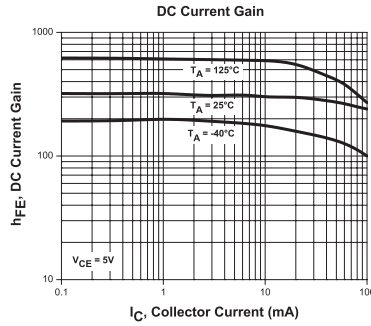
53,730

PRINCIPAL DEVICE TYPES

2N2605
2N3799
PN4250A
CMPT5086
CMPT5087

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